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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.		
10/700,085	11/03/2003	Tze-chiang Chen	YOR920030586US1 (17201)	2805		
23389 75	590 08/09/2005		EXAM	EXAMINER		
SCULLY SCO 400 GARDEN	OTT MURPHY & PI	NGUYEN, CU	NGUYEN, CUONG QUANG			
SUITE 300	CITTIEMEN	ART UNIT	PAPER NUMBER			
GARDEN CITY, NY 11530			2811			
			DATE MAILED, 00/00/2005			

Please find below and/or attached an Office communication concerning this application or proceeding.

		Applicatio	n No.	Applicant(s)	( M			
Office Action Summary		10/700,08	5	CHEN ET AL.	Class			
		Examiner		Art Unit				
		Cuong Q. N		2811				
Period fo	The MAILING DATE of this communicator Reply	tion appears on the	cover sheet with the c	correspondence addre	ess			
A SH THE - Exte after - If the - If NO - Failu Any	ORTENED STATUTORY PERIOD FOR MAILING DATE OF THIS COMMUNICA nsions of time may be available under the provisions of 3 SIX (6) MONTHS from the mailing date of this communic period for reply specified above is less than thirty (30) do period for reply is specified above, the maximum status into treply within the set or extended period for reply will, reply received by the Office later than three months after ed patent term adjustment. See 37 CFR 1.704(b).	TION. 7 CFR 1.136(a). In no ever cation. ays, a reply within the statur by period will apply and will by statute, cause the appli	nt, however, may a reply be tir tory minimum of thirty (30) day expire SIX (6) MONTHS from cation to become ABANDONE	nely filed  s will be considered timely. the mailing date of this commod (35 U.S.C. § 133).	nunication.			
Status								
- <sup>- ′</sup> 1)□	Responsive to communication(s) filed of	on .						
,	•	☐ This action is no	on-final.					
•—	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.							
Disposit	ion of Claims							
5)□ 6)⊠ 7)□	Claim(s) <u>1-68</u> is/are pending in the app 4a) Of the above claim(s) <u>2,8-10,15-28</u> Claim(s) is/are allowed. Claim(s) <u>1,3-7,11-14,29-32</u> is/are reject Claim(s) is/are objected to. Claim(s) are subject to restriction	<i>a<u>nd 33-68</u> is/a</i> re wi ted.		eration.				
Applicat	ion Papers							
10)	The specification is objected to by the E The drawing(s) filed on is/are: a Applicant may not request that any objectio Replacement drawing sheet(s) including the The oath or declaration is objected to by	correction is require	e held in abeyance. Send if the drawing(s) is ob	e 37 CFR 1.85(a). ejected to. See 37 CFR				
Priority	under 35 U.S.C. § 119							
12)□ a)	Acknowledgment is made of a claim for All b) Some * c) None of:  1. Certified copies of the priority do  2. Certified copies of the priority do  3. Copies of the certified copies of the application from the International See the attached detailed Office action for the certified copies of the attached detailed Office action for the certified copies of the attached detailed Office action for the certified copies of the attached detailed Office action for the certified copies of the certified copies of the certified copies of the priority do	cuments have beer cuments have beer the priority docume I Bureau (PCT Rule	n received. n received in Applicat nts have been receiv e 17.2(a)).	ion No ed in this National St	age			
2) Noti 3) Info	nt(s) ce of References Cited (PTO-892) ce of Draftsperson's Patent Drawing Review (PTO- mation Disclosure Statement(s) (PTO-1449 or PT er No(s)/Mail Date		4) Interview Summan Paper No(s)/Mail D 5) Notice of Informal 6) Other:		52)			

#### **DETAILED ACTION**

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## Claim Rejections - 35 USC § 112

1. The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

Claims 1, 3-7, 11-14 and 29-32 are rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the written description requirement. The claim(s) contains subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention. There is no support for the new limitation "a bonding interface is present between the substrate and the buried insulator layer" in claim 1 in elected Embodiment of Fig.1.

## Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

## A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- (a) the invention was known or used by others in this country, or patented or described in a printed publication in this or a foreign country, before the invention thereof by the applicant for a patent.

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Claims 1, 3, 4, 5, 11, 12 and 14 are rejected under 35 U.S.C. 102(a) as being anticipated by Bae et al. (US 6,633,066).

Regarding claims 1, 3, 4, 11, 12, Bae et al. discloses a semiconductor wafer comprising: a silicon (Si) substrate (20) (col.2 lines 36-40) performed silicon-on-insulators; a buried insulator layer (22) located on an upper surface of the substrate; an intermediate adhesion layer (18, an epitaxial silicon layer) located on an upper surface the buried insulator layer; and a Ge-containing layer (16) located on an upper surface of the intermediate adhesion layer, wherein said Ge-containing layer is attached to the buried insulator layer by the intermediate adhesion layer. Fig.4E.

It is noted that a bonding interface is inherently present between the substrate and the buried insulating layer.

Regarding claim 5, as shown in Bae et al.'s Fig.4E, that the substrate comprises a combination of strained and unstrained layers.

Regarding claim 14, Bae et al. teaches that the Ge-containing layer has a thickness of 80 nm (col.7 lines 31-32).

Claims 1, 3, 4, 6, 7, 11, 12 are rejected under 35 U.S.C. 102(b) as being anticipated by Chu et al. (US 5,906,951).

Chu et al. discloses a semiconductor wafer comprising: a silicon substrate (26) performed silicon-on-insulators; a buried insulator layer (28, a non-crystalline silicon dioxide layer) located on an upper surface of the substrate; an intermediate adhesion

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layer (19, an epitaxial silicon layer) located on an upper surface the buried insulator layer; and a Ge-containing layer (18) located on an upper surface of the intermediate adhesion layer, wherein said Ge-containing layer is attached to the buried insulator layer by the intermediate adhesion layer. Fig.4.

It is noted that a bonding interface is inherently present between the substrate and the buried insulating layer.

Claims 1, 3, 4, 6, 7, 11, 12, 13 and 29-32 are rejected under 35 U.S.C. 102(e) as being anticipated by Fitzergald (US 6,677,655).

Regarding claims 1, 3, 4, 6, 7, 11, 12, 13, Fitzergald discloses a semiconductor wafer comprising: a silicon substrate (308) performed silicon-on-insulators; a buried insulator layer (310, a non-crystalline silicon dioxide layer) located on an upper surface of the substrate; an intermediate adhesion layer (306, an epitaxial silicon layer) located on an upper surface the buried insulator layer; and a pure Ge layer (302) located on an upper surface of the intermediate adhesion layer, wherein said Ge-containing layer is attached to the buried insulator layer by the intermediate adhesion layer. Fig.3D.

It is noted that a bonding interface is inherently present between the substrate and the buried insulating layer.

Regarding claims 29-32, Fitzegald teach that a monolithic optoelectronic integrated circuit including a si-containing circuit is formed on the semiconductor wafer (col.1 lines 9-23) lemst one device or circuit located thereon. Fitzergald further teaches that the device is a Ge-photodetector (col.7 lines 30-40).

## Conclusion

2. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

3. Papers related to this application may be submitted to Technology center (TC) 2800 by facsimile transmission. Papers should be faxed to TC 2800 via the TC 2800 Fax center located in Crystal Plaza 4, room 4-C23. The faxing of such papers must conform with the notice published in the Official Gazette, 1096 OG 30 (November 15, 1989). The Group 2811 Fax Center number is (703) 872-9306. The Group 2811 Fax Center is to be used only for papers related to Group 2811 applications.

Any inquiry concerning this communication or any earlier communication from the Examiner should be directed to CUONG Q NGUYEN whose telephone number is (571) 272-1661. The Examiner is in the Office generally between the hours of 6:30 AM to 5:00 PM (Eastern Standard Time) Monday through Thursday.

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4. If attempts to reach the examiner by telephone are unsuccessful, the examiner's

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supervisor Eddie Lee who can be reached on (571) 272-1732.

5. Any inquiry of a general nature or relating to the status of this application should

be directed to the Technology Center Receptionists whose telephone number is 308-

0956.

Cuong Nguyen

Primary examiner

8/3/05